

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Sheet 1 of 3

C mpt te if Kn wn	
Application Number	10/660,813
Filing Date	September 12, 2003
First Named Inventor	Mungekar, Hemant P.
Art Unit	
Examiner Name	Not yet assigned
Attorney Docket Number	A8067/T51700

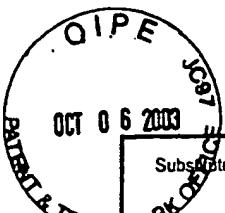
U.S. PATENT DOCUMENTS+

Examiner Initials*	Cite No. ¹	Document Number Number Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	US-4,690,746	09-01-1987	McInerney et al.	
	A2	US-4,737,379	04-12-1988	Hudgens et al.	
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	A5	US-4,890,575	01-02-1990	Ito et al.	
	A6	US-4,892,753	01-09-1990	Wang et al.	
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	A9	US-5,089,442	02-18-1992	Olmer	
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	A41	US-6,013,584	01-11-2000	M'Saad	

Examiner
Signature*Hemant P. Mungekar*Date
Considered

9/16/05

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Sheet 2 of 3

				Complete if Known
				Application Number 10/660,813
				Filing Date September 12, 2003
				First Named Inventor Mungekar, Hemant P.
				Art Unit
				Examiner Name Not yet assigned
				Attorney Docket Number A8067/T51700

U.S. PATENT DOCUMENTS+

Examiner Initials*	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A42	US-6,030,881	02-29-2000	Papasouliotis et al.	
	A43	US-6,037,018	03-14-2000	Jang et al.	
	A44	US-6,039,851	03-21-2000	Iyer	
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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
	B1	JP	7-161703	A	06-23-1995		Abstract only	<input type="checkbox"/>
	B2	JP	2058836	A	02-28-1990		Abstract only	<input type="checkbox"/>
	B3	GB	2 267 291		12-01-1993			<input type="checkbox"/>

Examiner Signature

Date Considered

9/10/05

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Substitute for form 1449B/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Application Number</i>	10/660,813
<i>(use as many sheets as necessary)</i>				<i>Filing Date</i>	September 12, 2003
				<i>First Named Inventor</i>	Mungekar, Hemant P.
				<i>Art Unit</i>	
				<i>Examiner Name</i>	Not yet assigned
Sheet	3	of	3	<i>Attorney Docket Number</i>	A8067/T51700

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
<i>pm</i>	C1	ABRAHAM, "Reactive Facet Tapering of Plasma Oxide For Multilevel Interconnect Applications," VMIC Conference, pgs. 115-121 (1987).		
	C2	LEE et al., "Dielectric Planarization Techniques For Narrow Pitch Multilevel Interconnects," VMIC Conference, pgs. 85-92 (1987).		
	C3	MUSAKA, "Single Step Gap Filling Technology fo Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O2 Chemical Vapor Deposition System," International Conference on Solid State Devices and Materials pgs. 510-512, held in Japan, (1993).		
	C4	NALWA, H.S., Handbook of Low and High Dielectric Constant Materials and Their Applications, vol. 1, page 66 (1999).		
	C5	NGUYEN, s.v., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits," Journal of Research and Development, vol. 43, 1/2 (1999).		
	C6	QIAN et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," DUMIC Conference, pgs. 50-56, held in California (1995).		
<i>h</i>	C7	VASSILIEV et al., "Trends in void-free pre-metal CVD dielectrics," <u>Solid State Technology</u> , 2001, pgs. 129-136, www.solid-state.com .		

Examiner Signature	<i>Hemant P. Mungekar</i>	Date Considered	<i>9/16/05</i>
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